V_{DSS}	30 V
I_D	200 mA
$R_{DS(ON)}$	3.5 Ω

KN

General Description

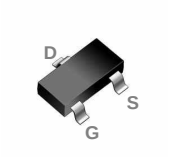
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

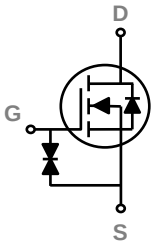
Features

30V,200mA, RDS(ON) =3.5Ω@VGS = 10V
Improved dv/dt capability
Fast switching
Green Device Available

Applications

Notebook
Load Switch
Battery Protection
Hand-held Instruments





MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_A=25℃)	200	mA
	Drain Current – Continuous (T_A=70℃)	150	mA
I_{DM}	Drain Current – Pulsed[1]	0.8	A
P_D	Power Dissipation (T_C=25℃)	200	mW
	Power Dissipation – Derate above 25℃	2.0	mW/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	400	℃/W

Electrical Characteristics (T_a=25℃unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
△BV_{DSS}/△T_J	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.05	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=50℃	---	---	100	nA
		V_{DS}=30V , V_{GS}=0V , T_J=75℃	---	---	400	nA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±6	uA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=0.2A	---	---	3.5	Ω
		V_{GS}=4.5V , I_D=0.1A	---	---	4.0	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.8	1.1	1.6	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3	---	mV/℃

Dynamic and switching Characteristics

C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , F=1MHz	---	23	---	pF
C_{oss}	Output Capacitance		---	16	---	
C_{rss}	Reverse Transfer Capacitance		---	10	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	200	mA
I_{SM}	Pulsed Source Current		---	---	400	mA
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=0.2A , T_J=25℃	---	---	1.3	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

RATING AND CHARACTERISTIC CURVES

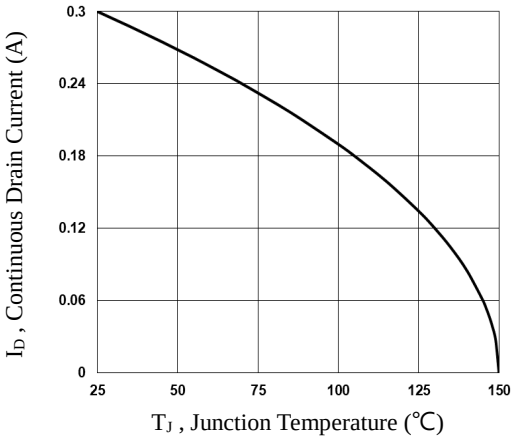


Fig.1 Continuous Drain Current vs. T_C

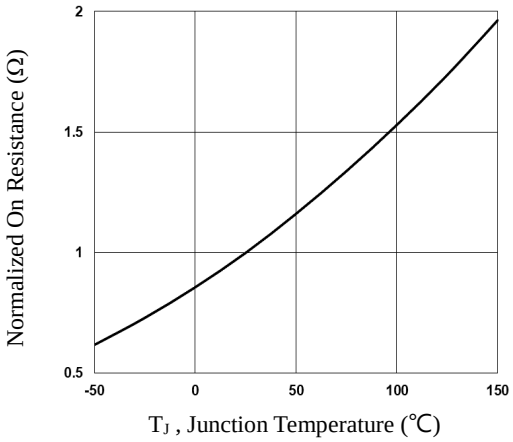


Fig.2 Normalized RDSON vs. T_J

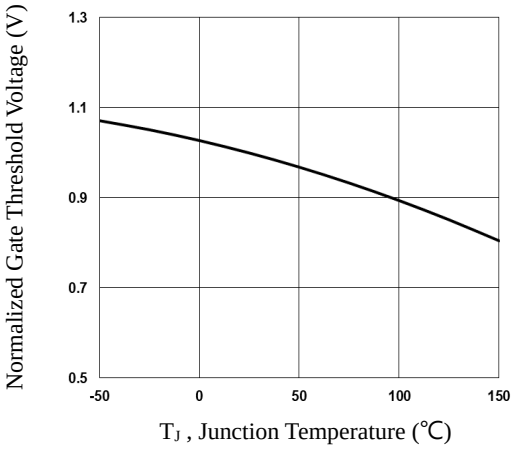


Fig.3 Normalized V_{th} vs. T_J

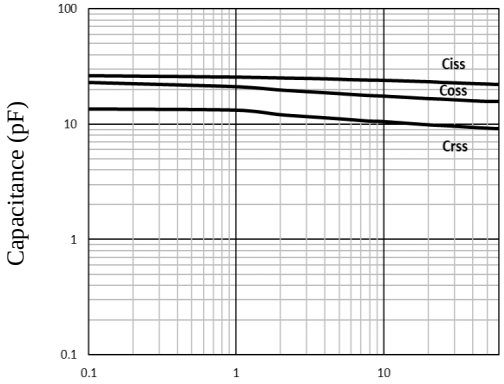


Fig.4 Capacitance Characteristics

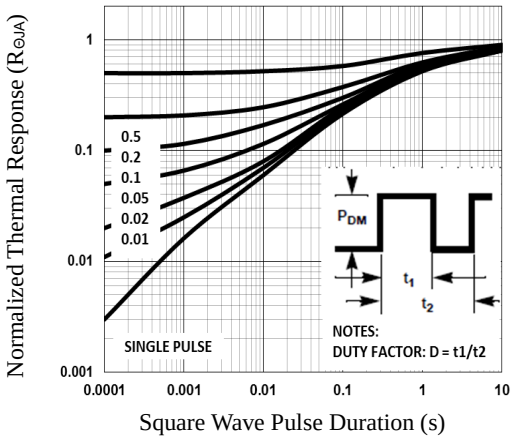


Fig.5 Normalized Transient Response

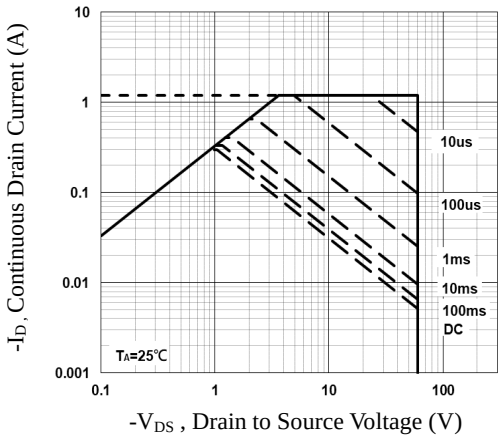


Fig.6 Maximum Safe Operation Area

RATING AND CHARACTERISTIC CURVES

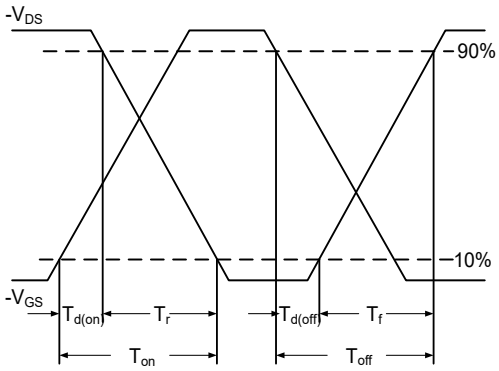


Fig.7 Switching Time Waveform

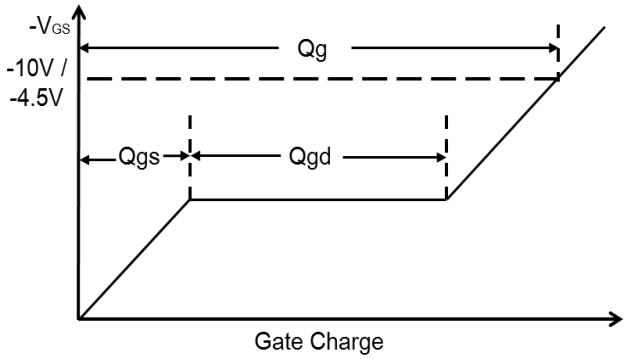
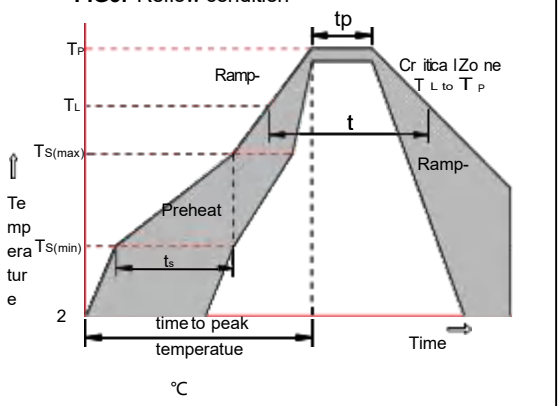


Fig.8 Gate Charge Waveform

Soldering parameters

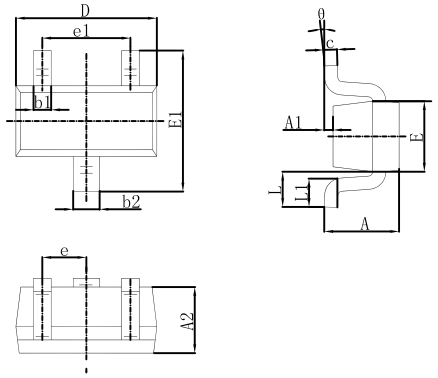
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition



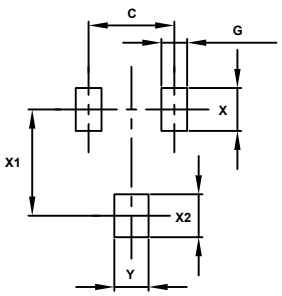
Package Dimensions & Suggested Pad Layout

SOT-523



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

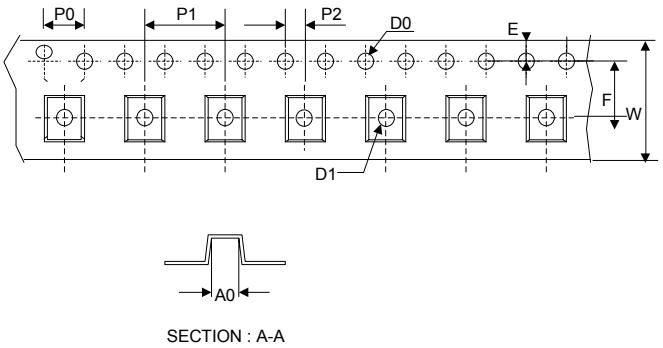
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	1.00
G	0.45
X	0.70
X1	1.40
X2	0.70
Y	0.60

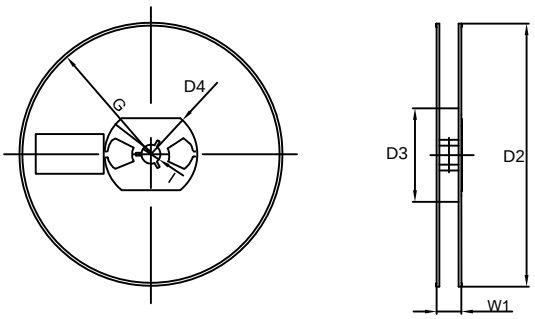
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	0.65±0.20
E	1.55±0.25
F	3.60±0.20
W	8.00±0.20
A0	2.10±0.20
B0	2.20±0.20
K0	1.10±0.20
T	0.20±0.20

7” Reel



D2	177.0±5.0
D3	55Min.
D4	R24.6±2.0
G	R82.0±2.0
I	13.0±2.0
W1	10.20±3.0

Quantity: 3000PCS

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